

# Robert M Farrell

## List of Publications by Year in descending order

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37  
papers

1,725  
citations

361413

20  
h-index

434195

31  
g-index

37  
all docs

37  
docs citations

37  
times ranked

1549  
citing authors

#	ARTICLE	IF	CITATIONS
1	Development of high performance green c-plane III-nitride light-emitting diodes. Optics Express, 2018, 26, 5591.	3.4	47
2	Zinc oxide clad limited area epitaxy semipolar III-nitride laser diodes. Optics Express, 2018, 26, 12490.	3.4	4
3	Semipolar GaN-based laser diodes for Gbit/s white lighting communication: devices to systems. , 2018, , .		9
4	Semipolar III-nitride laser diodes with zinc oxide cladding. Optics Express, 2017, 25, 16922.	3.4	8
5	Gigabit-per-second white light-based visible light communication using near-ultraviolet laser diode and red-, green-, and blue-emitting phosphors. Optics Express, 2017, 25, 17480.	3.4	75
6	Using tunnel junctions to grow monolithically integrated optically pumped semipolar III-nitride yellow quantum wells on top of electrically injected blue quantum wells. Optics Express, 2017, 25, 3841.	3.4	17
7	High luminous efficacy green light-emitting diodes with AlGaN cap layer. Optics Express, 2016, 24, 17868.	3.4	74
8	Dynamic characteristics of 410-nm semipolar (202̄1̄1̄) III-nitride laser diodes with a modulation bandwidth of over 5 GHz. Applied Physics Letters, 2016, 109, .	3.3	27
9	Measurement and analysis of internal loss and injection efficiency for continuous-wave blue semipolar (202̄1̄1̄) III-nitride laser diodes with chemically assisted ion beam etched facets. Applied Physics Letters, 2016, 108, .	3.3	21
10	Effects of active region design on gain and carrier injection and transport of CW semipolar InGaN laser diodes. Applied Physics Express, 2016, 9, 092104.	2.4	6
11	High-speed performance of III-nitride 410 nm ridge laser diode on (202̄1̄1̄) plane for visible light communication. , 2016, , .		1
12	Semipolar III-nitride light-emitting diodes with negligible efficiency droop up to 1/4 W. Applied Physics Express, 2016, 9, 102102.	2.4	26
13	Designing optically pumped InGaN quantum wells with long wavelength emission for a phosphor-free device with polarized white-light emission. , 2016, , .		0
14	High luminous flux from single crystal phosphor-converted laser-based white lighting system. Optics Express, 2016, 24, A215.	3.4	153
15	2 Gbit/s data transmission from an unfiltered laser-based phosphor-converted white lighting communication system. Optics Express, 2015, 23, 29779.	3.4	103
16	Demonstration of low resistance ohmic contacts to p-type (202̄1̄1̄) GaN. Semiconductor Science and Technology, 2015, 30, 075007.	2.0	12
17	4 Gbps direct modulation of 450 nm GaN laser for high-speed visible light communication. Optics Express, 2015, 23, 16232.	3.4	117
18	Valence band states and polarized optical emission from nonpolar and semipolar III-nitride quantum well optoelectronic devices. Japanese Journal of Applied Physics, 2014, 53, 100206.	1.5	34

#	ARTICLE	IF	CITATIONS
19	Surface Structured Optical Coatings with Near-Perfect Broadband and Wide-Angle Antireflective Properties. Nano Letters, 2014, 14, 5960-5964.	9.1	39
20	Influence of the Structure Parameters on the Relaxation of Semipolar InGaN/GaN Multi Quantum Wells. Japanese Journal of Applied Physics, 2013, 52, 08J10.	1.5	7
21	Comparison of Polished and Dry Etched Semipolar $(11\bar{1}2)$ III-Nitride Laser Facets. IEEE Photonics Technology Letters, 2013, 25, 2105-2107.	2.5	6
22	Study of Temperature-Dependent Carrier Transport in a p-GaN/i-InGaN/n-GaN Solar Cell Heterostructure using Ultrafast Spectroscopy. , 2013, , .		0
23	Effect of quantum well cap layer thickness on the microstructure and performance of InGaN/GaN solar cells. Applied Physics Letters, 2012, 100, .	3.3	53
24	Effect of doping and polarization on carrier collection in InGaN quantum well solar cells. Applied Physics Letters, 2011, 98, .	3.3	68
25	High internal and external quantum efficiency InGaN/GaN solar cells. Applied Physics Letters, 2011, 98, .	3.3	195
26	Blue InGaN/GaN laser diodes grown on $(3\bar{3}2)$ free-standing GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2390-2392.	0.8	7
27	AlGaIn-Cladding-Free $m$ -Plane InGaN/GaN Laser Diodes with p-Type AlGaIn Etch Stop Layers. Applied Physics Express, 2011, 4, 092105.	2.4	4
28	Observation of positive thermal power coefficient in InGaN/GaN quantum well solar cells. Applied Physics Letters, 2011, 99, 071104.	3.3	22
29	AlGaIn-Cladding Free Green Semipolar GaN Based Laser Diode with a Lasing Wavelength of 506.4 nm. Applied Physics Express, 2010, 3, 011002.	2.4	82
30	InGaN/GaN Blue Laser Diode Grown on Semipolar $(30\bar{1}1)$ Free-Standing GaN Substrates. Applied Physics Express, 2010, 3, 052702.	2.4	27
31	Continuous-Wave Operation of Pure Blue AlGaIn-Cladding-Free Nonpolar InGaN/GaN Laser Diodes. Applied Physics Express, 2010, 3, 092103.	2.4	27
32	Demonstration of Nonpolar $m$ -Plane InGaN/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L190-L191.	1.5	204
33	Continuous-wave Operation of AlGaIn-cladding-free Nonpolar $m$ -Plane InGaN/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L761.	1.5	83
34	AlGaIn-Cladding-Free Nonpolar InGaN/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L284-L286.	1.5	73
35	A semipolar $(10\bar{1}3)$ InGaN/GaN green light emitting diode. Materials Research Society Symposia Proceedings, 2005, 892, 418.	0.1	1
36	Blue-Green InGaN/GaN Laser Diodes on Miscut $m$ -Plane GaN Substrate. Applied Physics Express, 0, 2, 082102.	2.4	56

#	ARTICLE	IF	CITATIONS
37	Nonpolar AlGaIn-Cladding-Free Blue Laser Diodes with InGaIn Waveguiding. Applied Physics Express, 0, 2, 071003.	2.4	37